

Supporting Information:

Morphological evolution of hollow NiCo_2O_4 microsphere and its high pseudocapacitance contribution for Li/Na-ion batteries Anode

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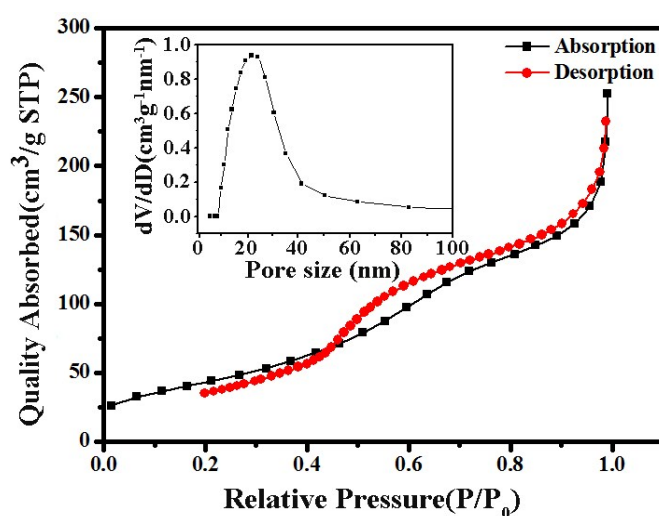


Fig.S1 N_2 adsorption-desorption isotherm and pore size distribution curve of hollow NiCo_2O_4 microspheres.

Table S1 Comparison of electrochemical Li-storage performance of our sample with some reported cobalt-based anodes for LIBs.

Ref.	Materials	Current density/ mA g^{-1}	Cycles	Initial capacity/ mAh g^{-1}	Last capacity/ mAh g^{-1}
[1]	rGO/ NiCo_2O_4	100	70	985	816
[2]	C/ NiCo_2O_4 @ SnO_2	100	100	1083	654
[3]	NiCo_2O_4 flows	100	60	1146	939
[4]	NiCo_2O_4 sheets	100	50	891	767
[5]	NiCo_2O_4 flakes	80	100	1056	981
[6]	NiCo_2O_4 @C	40	50	914.2	715.8
[7]	Plum-like NiCo_2O_4	100	50	855	820
[8]	NiCo_2O_4 nanosheets	200	100	1029.3	804.8
This work	hollow urchin-like NiCo_2O_4	100	50	1004.7	991

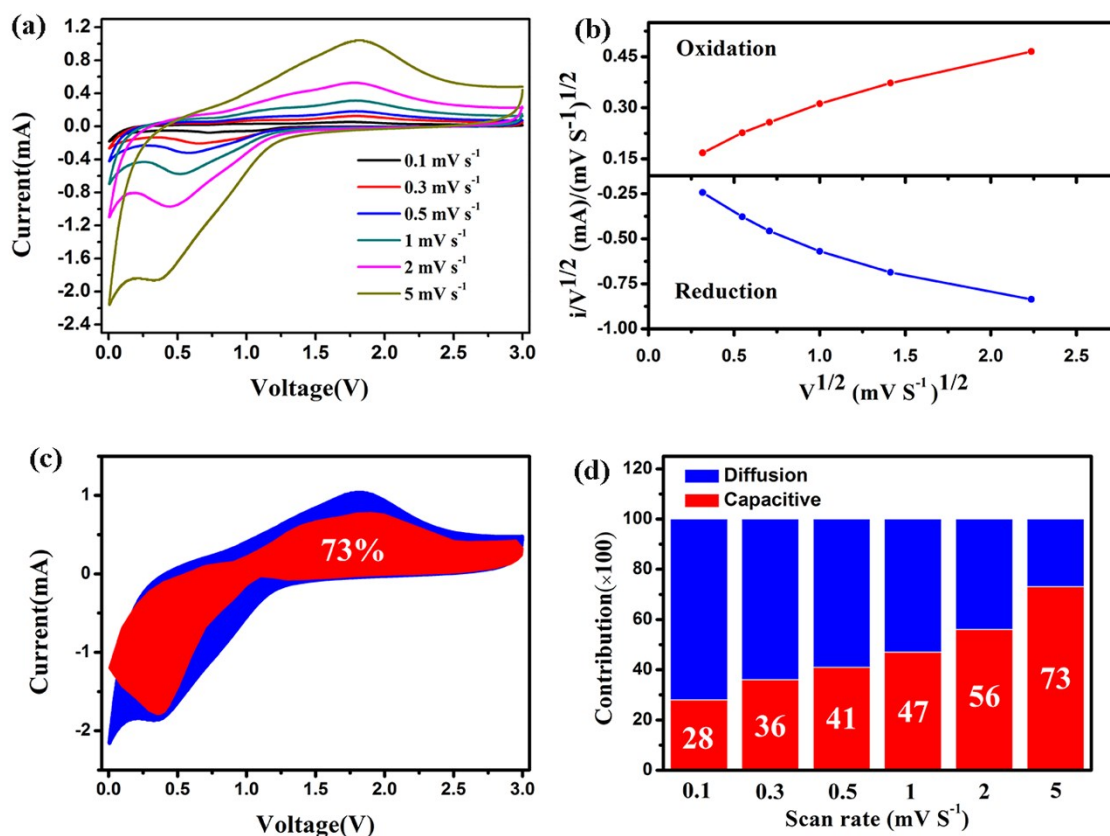


Fig.2 (a) CV curves at different sweep rates. (b) $i/v^{1/2}$ vs $v^{1/2}$ relationship (c) Capacitive (red) and diffusion-controlled (blue) contribution to charge storage at 0.3 mV s^{-1} . (d) Capacitive contribution of hollow NiCo_2O_4 microsphere at different scan rates as anode for SIBs.

Table S2 Comparison of electrochemical Na-storage performance of our sample with some reported cobalt-based anodes for SIBs.

Ref.	Materials	Current density/ mA g^{-1}	Cycles	Capacity retention/ mAh g^{-1}
[9]	NiCo_2O_4 @nanosheets	100	50	207
		200	50	203
[10]	NiCo_2O_4 @nanoneedle array	100	50	215
[11]	NiCo_2O_4 @CFC nanowire	50	50	542
		400	20	363
This work	hollow urchin-like NiCo_2O_4	100	50	322.3

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